

# **Absolute Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-160	V
Collector-Emitter Voltage	$V_{\sf CEO}$	-150	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Continuous Collector Current	Ic	-200	mA

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)	P <sub>D</sub>	200	mW
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C

## ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)						
Collector-Base Breakdown Voltage	$V_{CBO}$	-160		V	$I_C = -100 \mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage	V <sub>CEO</sub>	-150		V	$I_C = -1mA, I_B = 0$	
Emitter-Base Breakdown Voltage	V <sub>EBO</sub>	-5	_	V	$I_E = -100 \mu A, I_C = 0$	
Collector Cutoff Current	I <sub>CBO</sub>	_	-50	nΑ μΑ	$V_{CB} = -120V, I_{E} = 0$ $V_{CB} = -120V, I_{E} = 0, T_{A} = +100^{\circ}C$	
Emitter Cutoff Current	I <sub>EBO</sub>	_	-50	nA	$V_{EB} = -3V, I_{C} = 0$	
ON CHARACTERISTICS (Note 8)						
DC Current Gain	h <sub>FE</sub>	50 60 50	240 —	_	$\begin{split} I_{C} &= -1 mA \;,\; V_{CE} = -5 V \\ I_{C} &= -10 mA \;,\; V_{CE} = -5 V \\ I_{C} &= -50 mA \;,\; V_{CE} = -5 V \end{split}$	
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		-0.2 -0.5	V	$I_{C} = -10mA, I_{B} = -1mA$ $I_{C} = -50mA, I_{B} = -5mA$	
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>		-1	V	$I_{C} = -10\text{mA}, I_{B} = -1\text{mA}$ $I_{C} = -50\text{mA}, I_{B} = -5\text{mA}$	
SMALL SIGNAL CHARACTERISTICS	SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C <sub>obo</sub>		6.0	pF	$V_{CB} = -10V$ , $f = 1MHz$ , $I_E = 0$	
Small Signal Current Gain	h <sub>fe</sub>	40	260		$V_{CE} = -10V$ , $I_C = -1mA$ , $f = 1kHz$	
Current Gain-Bandwidth Product	f⊤	100	300	MHz	$V_{CE} = -10V, I_{C} = -10mA,$ f = 100MHz	
Noise Figure	NF	_	8	dB	$V_{CE}$ = -5V, $I_{C}$ = -200 $\mu$ A, $R_{S}$ =10 $\Omega$ , $f$ = 1kHz	

<sup>6.</sup> For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

8. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.



## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

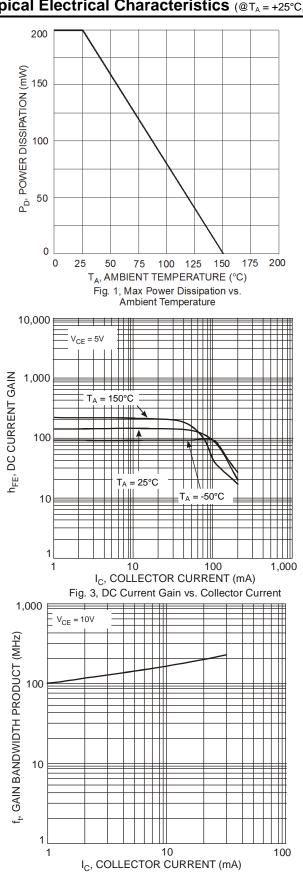
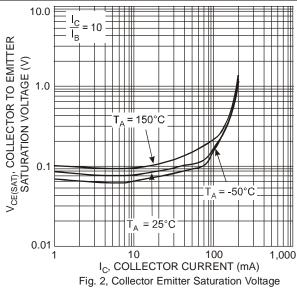


Fig. 5, Gain Bandwidth Product vs. Collector Current



vs. Collector Current 1.0 0.9 V<sub>BE(ON)</sub>, BASE EMITTER VOLTAGE (V) T<sub>A</sub> = -50°C 0.8 0.7  $T_A = 25^{\circ}C$ 0.6 0.5 0.4  $T_A = 150^{\circ}C$ 0.3 0.2 0.1 0.1 10 I<sub>C</sub>, COLLECTOR CURRENT (mA)

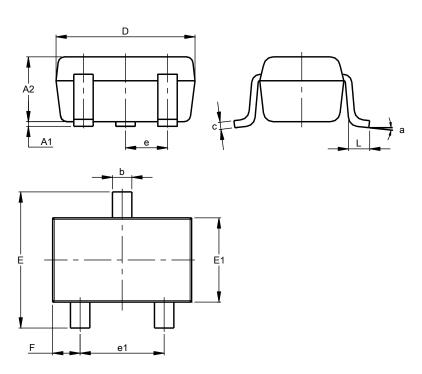
Fig. 4, Base Emitter Voltage vs. Collector Current



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT323**

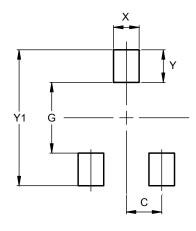


SOT323					
Dim	Min	Max	Тур		
A1	0.00	0.10	0.05		
A2	0.90	1.00	0.95		
b	0.25	0.40	0.30		
C	0.10	0.18	0.11		
D	1.80	2.20	2.15		
Е	2.00	2.20	2.10		
E1	1.15	1.35	1.30		
е	0.650 BSC				
e1	1.20	1.40	1.30		
F	0.375	0.475	0.425		
L	0.25	0.40	0.30		
а	0°	8°			
All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT323**



Dimensions	Value (in mm)
С	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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